

Fast switching diode chip in EMCON-Technology

FEATURES:

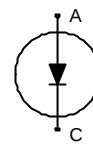
- 1200V EMCON technology 120 μm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- EUPEC power modules and discrete devices

Applications:

- SMPS, resonant applications, drives



Chip Type	V _{CE}	I _{CN}	Die Size	Package	Ordering Code
SIDC08D120H	1200V	12A	2.20 x 3.70 mm ²	sawn on foil	Q67050-A4110-A001

MECHANICAL PARAMETER:

Raster size	2.20 x 3.70	mm ²
Area total / active	8.14 / 4.73	
Anode pad size	1.48 x 2.98	
Thickness	120	μm
Wafer size	125	mm
Flat position	180	deg
Max. possible chips per wafer	1208	
Passivation frontside	Photoimide	
Anode metalization	3200 nm Al Si 1%	
Cathode metalization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, $\leq 500\mu\text{m}$	
Reject Ink Dot Size	tbd	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month	

Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continuous forward current limited by T_{jmax}	I_F		12	A
Single pulse forward current (depending on wire bond configuration)	I_{FSM}	$t_P = 10\text{ ms sinusoidal}$	tbd	
Maximum repetitive forward current limited by T_{jmax}	I_{FRM}		24	
Operating junction and storage temperature	T_J, T_{stg}		-55...+150	°C

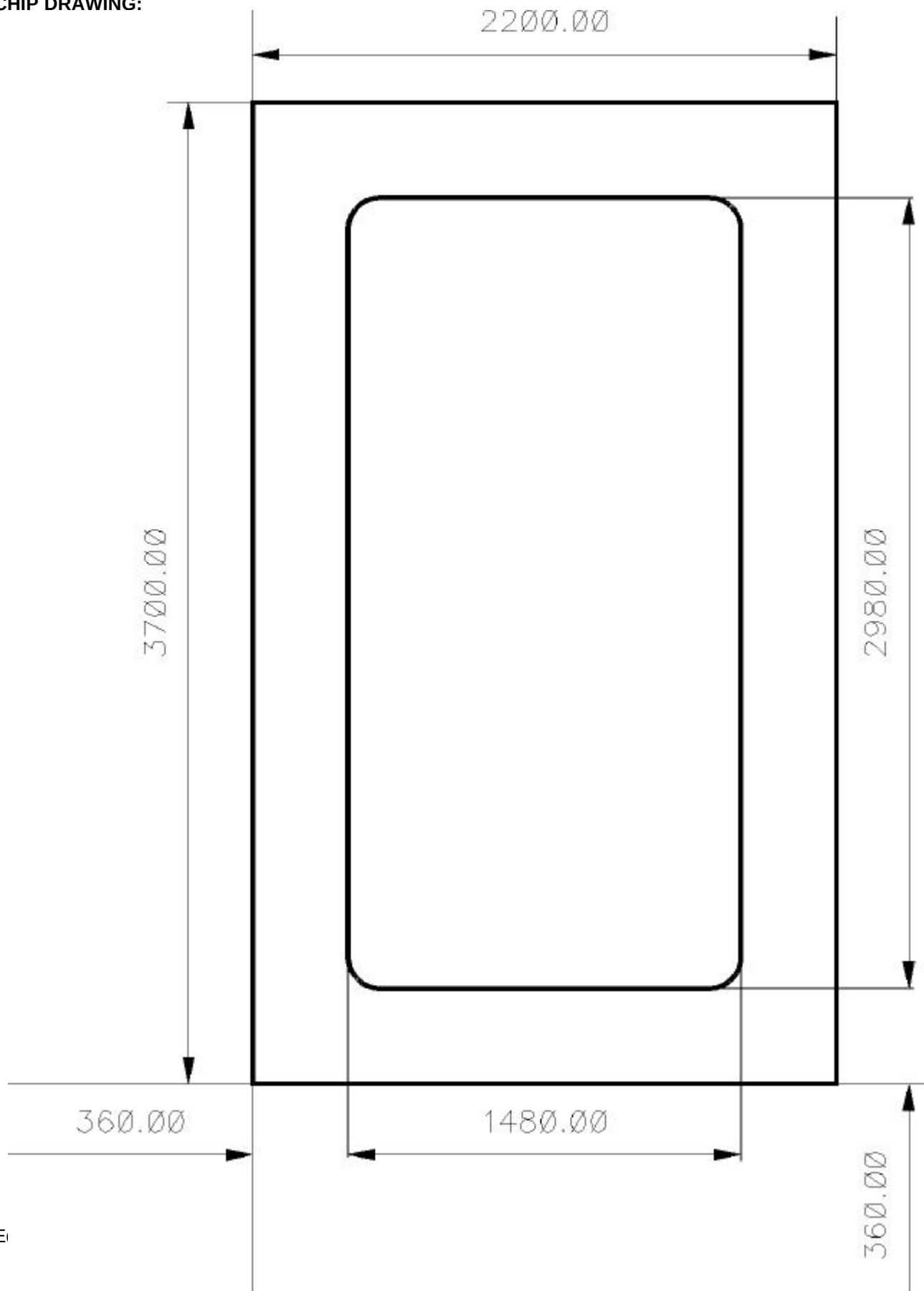
Static Electrical Characteristics (tested on chip), $T_J=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse leakage current	I_R	$V_R=1200\text{ V}$	$T_J=25\text{ °C}$			250	µA
Cathode-Anode breakdown Voltage	V_{Br}	$I_R=800\text{ µA}$	$T_J=25\text{ °C}$	1200			V
Forward voltage drop	V_F	$I_F=(10)12\text{ A}$	$T_J=25\text{ °C}$		(1.6)1.8		V

Dynamic Electrical Characteristics, at $T_J = 25\text{ °C}$, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse recovery time	t_{rr1}	$I_F=12\text{ A}$	$T_J = 25\text{ °C}$		tbd		ns
	t_{rr2}	$di/dt=tbd\text{ A/ms}$ $V_R=600\text{ V}$	$T_J = 150\text{ °C}$				
Peak recovery current	I_{RRM1}	$I_F=12\text{ A}$	$T_J = 25\text{ °C}$		tbd		A
	I_{RRM2}	$di/dt=tbd\text{ A/ms}$ $V_R= 600\text{ V}$	$T_J = 150\text{ °C}$				
Reverse recovery charge	Q_{rr1}	$I_F=12\text{ A}$	$T_J=25\text{ °C}$		tbd		nC
	Q_{rr2}	$di/dt=tbd\text{ A/ms}$ $V_R= 600\text{ V}$	$T_J=150\text{ °C}$				
Peak rate of fall of reverse recovery current	di_{rr1}/dt	$I_F=12\text{ A}$	$T_J=25\text{ °C}$		tbd		A/µs
	di_{rr2}/dt	$di/dt=tbd\text{ A/ms}$ $V_R= 600\text{ V}$	$T_J=150\text{ °C}$				
Softness	S1	$I_F=12\text{ A}$	$T_J=25\text{ °C}$		tbd		1
	S2	$di/dt=tbd\text{ A/ms}$ $V_R= 600\text{ V}$	$T_J=150\text{ °C}$				

CHIP DRAWING:





Preliminary

SIDC08D120H

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the
device data sheet

INFINEON TECHNOLOGIES /
EUPEC

tbd

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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